

RoHS

Phase Control Thyristors (Stud Version), 330 A

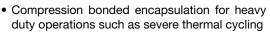


TO-118 (TO-209AE)

PRIMARY CHARACTERISTICS			
I _{T(AV)}	330 A		
V _{DRM} /V _{RRM}	400 V, 800 V, 1200 V, 1400 V, 1600 V, 2000 V		
V _{TM}	1.52 V		
l _{GT}	200 mA		
TJ	-40 °C to +125 °C		
Package	TO-118 (TO-209AE)		
Circuit configuration	Single SCR		

FEATURES

- Center amplifying gate
- International standard case TO-118 (TO-209AE)
- Hermetic metal case with ceramic insulator



- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- · DC motor controls
- · Controlled DC power supplies
- · AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
		330	A		
I _{T(AV)}	T _C	75	°C		
I _{T(RMS)}		520			
I _{TSM}	50 Hz	9000	A		
	60 Hz	9420			
121	50 Hz	405	1.42-		
I ² t	60 Hz	370	– kA ² s		
V _{DRM} /V _{RRM}		400 to 2000	V		
tq	Typical	100	μs		
T _J		-40 to +125	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$\begin{split} I_{DRM}/I_{RRM} & \text{MAXIMUM AT} \\ T_J = T_J & \text{MAXIMUM} \\ & \text{mA} \end{split}$			
	04	400	500				
	08	800	900				
VS-ST330S	12	1200	1300	50			
VO 010000	14	1400	1500	30			
	16	1600	1700				
	20	2000	2100				



ABSOLUTE MAXIMUM RATINGS	S					
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	I	180° condu	180° conduction, half sine wave		330	Α
at case temperature	$I_{T(AV)}$				75	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 75 °C	case temperati	ure	520	
		t = 10 ms	No voltage		9000	
Maximum peak, one-cycle	L	t = 8.3 ms	reapplied		9420	A kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}	Sinusoidal half wave, initial $T_J = T_J$ maximum	7570	
		t = 8.3 ms	reapplied		7920	
Maximum I ² t for fusing	l ² t	t = 10 ms	No voltage		405	
		t = 8.3 ms	reapplied		370	
		t = 10 ms	100 % V _{RRM}		287	
		t = 8.3 ms	reapplied		262	
Maximum I ² √t for fusing	I²√t	t = 0.1 to 10 ms, no voltage reapplied		4050	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		$I_{T(AV)}$), $T_J = T_J$ maximum	0.834	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		0.898] v	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		0.687	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		0.636	11152	
Maximum on-state voltage	V_{TM}	$I_{pk} = 1000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$		1.52	V	
Maximum holding current	I _H			600	mΛ	
Typical latching current	ΙL	T _J = 25 °C, anode supply 12 V resistive load			1000	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dI/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs
Typical delay time	t _d	Gate current A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0	
Typical turn-off time	t _q	I_{TM} = 550 A, T_J = T_J maximum, dl/dt = 40 A/μs, V_R = 50 V, dV/dt = 20 V/μs, gate 0 V 100 Ω , t_p = 500 μs	100	μs

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs	
Maximum peak reverse and off-state leakage current	I _{RRM,} I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	50	mA	



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
PARAMETER	STINIBUL	15	SI CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10.0		W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2.	.0	VV
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \leq 5 \; ms$	3.	.0	Α
Maximum peak positive gate voltage	+V _{GM}	T - T movimum	+ < 5 ma	20		
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms		5.0		V
				200	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	100	200	mA
		T _J = 125 °C		50	-	
		T _J = -40 °C		2.5	-	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C		1.8	3	V
		T _J = 125 °C		1.1	-	
DC gate current not to trigger	I _{GD}	T. T. magyimay	Maximum gate current/voltage not to trigger is the maximum	10		mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J$ maximum	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		-40 to +125	°C	
Maximum storage temperature range	T _{Stg}		-40 to +150		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.10	K/W	
Maximum thermal resistance, case to heatsink	R _{thC-hs}	Mounting surface, smooth, flat and greased	0.03	r√vv	
Mounting torque, ± 10 %		Non-lubricated threads	48.5 (425)	N ⋅ m (lbf ⋅ in)	
Approximate weight			535	g	
Case style		See dimension - link at the end of datasheet	TO-118 (TO-	-209AE)	

△R _{thJC} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS		
180°	0.011	0.008				
120°	0.013	0.014				
90°	0.017	0.018	$T_J = T_J$ maximum	K/W		
60°	0.025	0.026				
30°	0.041	0.042				

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

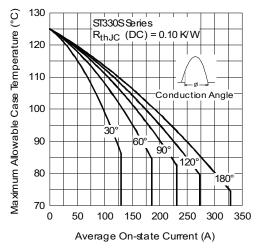


Fig. 1 - Current Ratings Characteristics

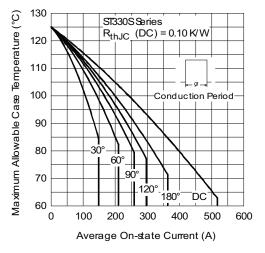


Fig. 2 - Current Ratings Characteristics

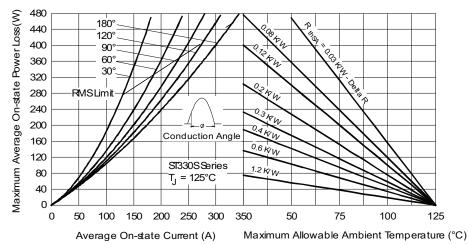


Fig. 3 - On-State Power Loss Characteristics

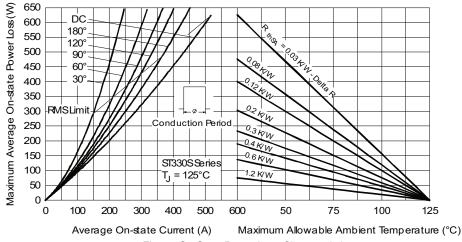


Fig. 4 - On-State Power Loss Characteristics

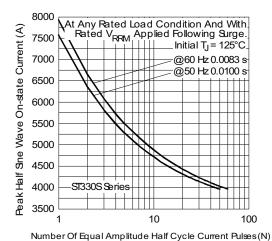


Fig. 5 - Maximum Non-Repetitive Surge Current

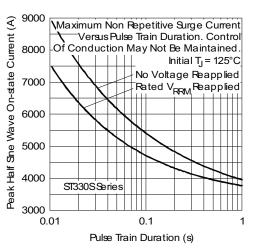


Fig. 6 - Maximum Non-Repetitive Surge Current

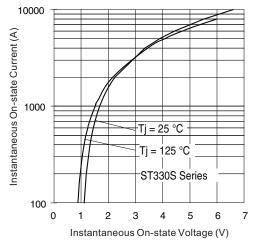


Fig. 7 - On-State Voltage Drop Characteristics

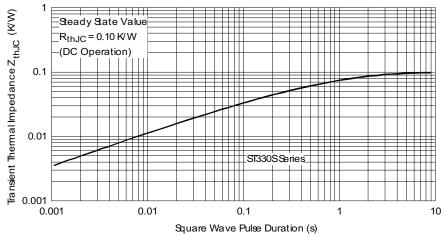


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

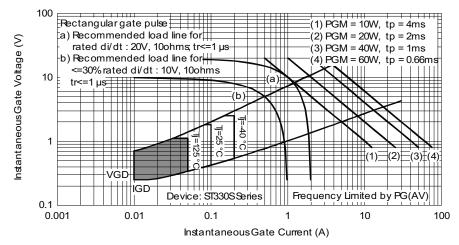
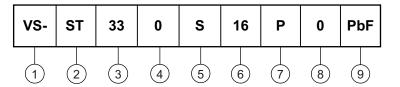


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Thyristor
- 3 Essential part number
- 4 0 = converter grade
- 5 S = compression bonding stud
- 6 Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 7 P = stud base 3/4"-16UNF-2A threads

M = stud base metric threads (M24 x 1.5)

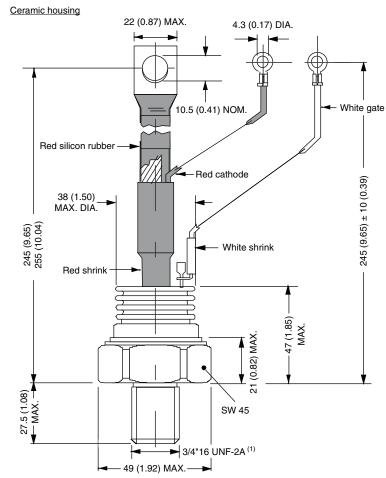
- 8 0 = eyelet terminals (gate and auxiliary cathode leads)
 - 1 = fast-on terminals (gate and auxiliary cathode leads)
- 9 None = standard production
 - PbF = lead (Pb)-free

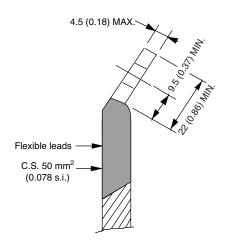
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95080

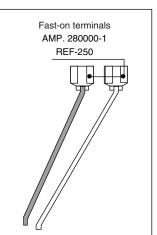


TO-209AE (TO-118)

DIMENSIONS in millimeters (inches)







Note

(1) For metric device: M24 x 1.5 - length 21 (0.83) maximum



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